Infrared Light Emitting Diode OPR2800, OPR2800T



Features:

- High-power GaAIAs
- Matches PLCC-2 footprint
- 880 nm wavelength
- Wide beam angle
- Wide operating temperature range (-40° C to +100° C)



Description:

The **OPR2800** is a GaAIAs infrared LED mounted in a surface mount chip carrier (SMCC) package with a flat lens window that allows a wide beam angle. The SMCC format has a lower height profile than the PLCC-2 package and mounts in the same footprint. The device is suitable for use in single device or array applications. The OPR2800 is spectrally matched to the OPR5500 phototransistor.

Applications:

- Non-contact position sensing
- Datum detection
- Machine automation
 Optical opcoding
- Optical encoding

| | Ordering Information | | | | | | |
|----------------|------------------------|---------------------|-------------|--|--|--|--|
| Part Number | LED Peak Wavelength | Total Beam Angle | Packaging | | | | |
| OPR2800 | 890 pm | 100° | Waffle Pack | | | | |
| OPR2800T | 860 1111 | 100 | Tape & Reel | | | | |



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Absolute Maximum Ratings (T_A = 25° C unless otherwise noted)

| Storage Temperature Range | -40° C to +100° C |
|--|-----------------------|
| Operating Temperature Range | -40° C to +100° C |
| Reverse Voltage | 30 V |
| Continuous Forward Current | 50 mA |
| Solder reflow time within 5°C of peak temperature is 20 to 40 seconds ⁽¹⁾ | 250° C |
| Power Dissipation | 130 mW ⁽²⁾ |

Electrical Characteristics (T_A = 25° C unless otherwise noted)

| SYMBOL | PARAMETER | MIN | ТҮР | MAX | UNITS | TEST CONDITIONS | |
|----------------------|-------------------------------------|-----|-----|------|--------------------|--|--|
| E _{E (APT)} | Apertured Radiant Incidence | 0.2 | - | - | mW/cm ² | I _F = 20 mA ⁽³⁾ | |
| V _F | Forward Voltage | - | - | 1.50 | V | I _F = 50 mA | |
| I _R | Reverse Current | - | - | 100 | μA | V _R = 2.0 V | |
| λ _P | Wavelength at Peak Emission | | 890 | - | nm | I _F = 10 mA | |
| θ_{HP} | Emission Angle at Half Power Points | - | 100 | - | Degree | I _F = 20 mA | |
| tr | Output Rise Time, Output Fall Time | - | - | 500 | ns | I _{F(PK)} = 100 mA, PW = 10 μs, D.C. = 10.0% | |
| t _f | Output Rise Time, Output Fall Time | - | - | 500 | ps | | |

Notes:

1. Solder time less than 5 seconds at temperature extreme.

2. Derate linearly at 1.73 mW/° C above 25° C.

 EE_(APT) is a measurement of the apertured radiant incidence upon a sensing area 0.081" (2.06 mm) in diameter, perpendicular to and centered on the mechanical axis of the lens and 0.590" (14.99 mm) from the measurement surface. EE_(APT) is not necessarily uniform within the measured area.



OP2800



OPTEK reserves the right to make changes at any time in order to improve design and to supply the best product possible.